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最新トランジスタ規格表 (New Transistor Manual) lists all the transistors registered with the Electronic Industries Association of Japan (EIAJ), arranged in a manner easy to look up. We hope that you will make full use of the data provided in this manual by referring to the Japanese-English translation key given below.

型名	社名	用途	構造	最大定格 (T _b =25°C)					電気的特性 (T _b =25°C)										備考		
				V _{ceo} (V)	V _{ceo} (V)	I _c (mA)	P _c (mW)	T _j (°C)	I _{ceo} 最大値 (μA)	直流又はパルスI _{BE}		バイアス		h _{FE}	h _{ie} h _{ie} * (Ω)	h _{re} h _{re} * (×10 ⁻⁴)	h _{oe} h _{oe} * (μS)	f _{αb} f _r * (Mc)		C _{ob} (pF)	r _{bb'} h _{ie} (real)* (Ω)
1	2	3	4	5					6		7		8				9	10		11	12

- 1 TYPE NUMBER
- 2 ORIGINAL MANUFACTURER
- 3 USES
- 4 MATERIAL AND STRUCTURE
- 5 MAXIMUM RATINGS
- 6 I_{CBO} MAXIMUM VALUE AND V_{CB} VALUE (CRITERIA FOR MEASURING I_{CBO})
- 7 STANDARD VALUE OF DC/PULSE h_{FE} AND V_{CE}, I_C (CRITERIA FOR MEASURING DC/PULSE h_{FE})
- 8 STANDARD VALUE OF h PARAMETERS AND BIAS V_{CB}, I_E (CRITERIA FOR MEASURING h PARAMETERS)

- * INDICATES VALUE IN GROUNDED-BASE OPERATION, OTHERWISE VALUE IN EMITTER-GROUNDED OPERATION.
 - 9 f_{αb} OF RF CHARACTERISTIC, EXCEPT IN CASE OF * WHICH INDICATES VALUE OF f_r.
 - 10 C_{ob} AND r_{bb'} OF RF CHARACTERISTICS EXCEPT IN CASE OF * IN r_{bb'} COLUMN WHICH INDICATES VALUE OF h_{ie} (real)
 - 11 OUTLINE
 - 12 REMARKS
- :とコンプリ: COMPLEMENTARY TO

型名	社名	用途	構造	最大定格 (T _a = 25°C)					電 気 的 特 性 (T _a = 25°C)										外 形	備 考				
				V _{CB0} (V)	V _{EBO} (V)	I _c (mA)	P _c (mW)	T _j (°C)	I _{CB0} 最大 ⁴⁾		直流又はパルス hFE		バイアス		h _{fe} h _{fb} *	h _{ie} h _{ib} * (Ω)	h _{re} h _{rb} * (×10 ⁻⁴)	h _{oe} h _{ob} * (μU)			f _β f _T * (Mc)	C _{ob} (pF)	τ _{ββ} h _{ie} (real)* (Ω)	
									μA	V _{CB} (V)	V _{CE} (V)	I _C (mA)	V _{CB} (V)	I _B (mA)										h _{fb} *
2SC624	協同	SW	Si.EP	40	4.5	200	300	150	0.5	20	60	1	10								28	KT-2103		
" 625	"	"	"																					
" 626	日電	RF.Conv.Mix Osc. PA	Si.E	50	5	200	750	175	0.1	20								350*	4	45*	84B			
" 627	富士通	RF.AF.SW	Si.T	200	4	100	700	175	5	100	80	10	50	6	-2	50	1000	0.8	10	20*	6	25	84B	
" 628	日電	RF.PA	Si.E	40	4	500	2.5W (T _c =25°C)	175	0.4	20	40	10	100	10	-30	40	P _o = 2W (f = 200Mc, V _{cc} = 15V)		700*	5.5	40*	84B		
" 629	ソニー	RF.Conv Mix. Osc	Si.DB	18		30	150	120	0.2	15	30	3	1	6	-1	36				800*	1.3	C _c τ _{ββ} 15pS	38	
" 630	"	"	"																					
" 631	ソニー	RF.AF.LN	Si.E	25	6	100	250	120	0.2	25	350	3	1	6	-0.1		36k	2.4	3.3	140*	4.5	C _c τ _{ββ} 350pS	38	
" 632	"	RF.LN	"	40	6	100	250	120	0.2	25	350	3	1	6	-0.1		36k	2.4	3.3	140*	4.5	C _c τ _{ββ} 350pS	38	
" 633	"	RF.Conv.Mix Osc. SW	"	25	6	100	250	120	0.2	25	400	3	1	6	-2		t _r < 60nS, t _f < 150nS t _{stc} < 500nS		140*	4.5	C _c τ _{ββ} 350pS	38		
" 634	"	"	"	40	6	100	250	120	0.2	25	400	3	1	6	-2		t _r < 60nS, t _f < 150nS t _{stc} < 500nS		140*	4.5	C _c τ _{ββ} 350pS	38		
" 635	日電	PA	Si.E	65	4	1.5A	10W (T _c =25°C)	175	3	18	15-200	10	500	18	-150	50	P _o > 4W (f = 175Mc, V _{cc} = 18V)		450*	10	10*	111		
" 636	"	"	"	65	4	3A	20W (T _c =25°C)	175	10	18	15-200	10	1A	18	-150	50	P _o > 7W (f = 260Mc)		350*	16	8*	111		
" 637	"	"	"	40	4	1A	10W (T _c =25°C)	175	10	20	>20	13.5	500	13.5	-100	50				500*	16.5	10*	111	
" 638	"	"	"	40	4	2A	20W (T _c =25°C)	175	20	20	>20	13.5	1A	13.5	-200	50				400*	28	8*	111	
" 639	"	SW	"	40	5	200	360	200	0.1	20	90	1	10	10	-10		t _{on} < 12nS, t _{off} < 18nS t _s < 3nS		750*	1.8		49C		
" 640	"	RF	"	30	5	100	150	150	0.1	25	270	3	0.5	3	-0.5	300	15kΩ	16	3	100*	8	30*	23	
" 641	日立	SW.RF	Si.EP	40	5	100	100	125	0.25	20	45-160	0.5	1	10	-10		t _{on} = 20nS, t _{off} = 35nS t _s = 12nS		400*	< 6		138		
" 642	東芝	PA	Si.TMe	1100	5	1A	50W (T _c =25°C)	150	10	500	30-160	15	150	15	-200					2*	55	10	102	水平偏向用
" 643	"	"	"	1100	5	2.5A	50W (T _c =25°C)	150	10	500	> 7	15	2A	15	-200					> 2	80	10	102	
" 644	松下	RF.AF.LN	Si.EP	30	5	50	150	125	1	10	250	5	2	5	-2	200	5000	0.7	10	160*	2.3	C _c τ _{ββ} 110pS	138	
" 645	"	RF.Conv.Mix Osc	"	30	5	30	140	175	1	10	40-150	10	1	10	-1	100				200*	0.65	22	243	
" 646	"	PA	Si.TMe	60	5	4A	25W (T _c =25°C)	150	10mA	60	55	4	2.5A	4	-100	70				50*	110	12	102	
" 647	"	"	"	80	5	5A	50W (T _c =25°C)	150	10mA	60	40	4	4A	10	500					43*	160	7	102	
" 648	日立	RF	Si.E	30	30	100	150	150	0.1	20	280	6	0.1	5	-0.1	320	17kΩ	1.9	12	350*	1.7	80*	182C	
" 649	"	RF.AF.LN	"	30	6	30	200	175	0.1	20	120	6	0.1	5	-0.1	150	36kΩ	9.4	3.1	220*	2.7	85	12A	
" 650	"	"	"	30	6	30	200	175	0.1	20	250	6	0.1	5	-0.1	300	86kΩ	2.8	8.5	220*	2.7	75	12A	
" 651	日電	PA	"	45	4	300	750	150	0.1	20	20-200	10	100	10	-30	80				1100*	2.4	27*	84B	
" 652	"	"	"	40	3	300	750	150	0.2	20	>20	10	100	10	-30	80				1100*	2.4	27*	84B	
" 653	"	RF	"	25	3	20	200	150	0.1	12				6	-2	120	NF < 4dB (1Mc) NF < 22dB (1kc)		1400*	0.6	60*	50C		